









SN74LVC1G126-Q1

JAJSI35D - JULY 2003 - REVISED AUGUST 2020

# SN74LVC1G126-Q1 シングル・バス・バッファ・ゲート、3 ステート出力

# 1 特長

- 車載アプリケーション認定済み
- 5V V<sub>CC</sub> 動作をサポート
- 5.5V までの入力電圧に対応
- V<sub>CC</sub> への降圧変換をサポート
- 低消費電力、最大 I<sub>CC</sub>: 10μA
- 3.3V において ±24mA の出力駆動能力
- Ioff により活線挿抜、部分的パワーダウン・モード、バッ ク・ドライブ保護をサポート
- JESD 78、Class II 準拠で 100mA 超のラッチアップ性能

# 2 アプリケーション

- ケーブル・モデム終端システム
- 高速データ・アクイジションおよび生成
- モータ制御:高電圧
- 電力線通信モデム
- SSD:内蔵または外付け
- ビデオ放送およびインフラ:スケーラブルなプラットフォ
- ビデオ放送: IP ベース・マルチ・フォーマット・トランスコ ーダ
- ビデオ通信システム

## 3 概要

SN74LVC1G126-Q1 は、3 ステート出力に対応したシン グル・ライン・ドライバです。出力イネーブル入力が LOW になると、出力はディセーブルされます。

#### 製品情報

部品番号	パッケージ (ピン) <sup>(1)</sup>	本体サイズ	
1P1G126QDBVRQ1	SOT-23 (5)	2.90mm × 1.60mm	
1P1G126QDRYRQ1	SON (6)	1.00mm × 1.00mm	

(1) 利用可能なすべてのパッケージについては、このデータシートの 末尾にある注文情報を参照してください。





# Table of Contents

I	able of	Contents	
1 特長		8.3 Feature Description	
2 アプリケーション		9 Application and Implementation	
3 概要		9.1 Application Information	
4 Revision History 5 Pin Configuration and Functions		9.2 Typical Application	
6 Specifications		10 Power Supply Recommendations	
6.1 Absolute Maximum Ratings		11 Layout	
6.2 ESD Ratings		11.1 Layout Guidelines	12
6.3 Recommended Operating Conditions		11.2 Layout Example	
6.4 Thermal Information		12 Device and Documentation Support	13
6.5 Electrical Characteristics		12.1 Receiving Notification of Documentation Upda	
6.6 Switching Characteristics	7	12.2 Support Resources	13
6.7 Operating Characteristics		12.3 Trademarks	13
6.8 Typical Characteristics		12.4 静電気放電に関する注意事項	
7 Parameter Measurement Information		12.5 Glossary	13
8 Detailed Description	9	13 Mechanical, Packaging, and Orderable	
8.1 Overview	9	Information	13
8.2 Functional Block Diagram	9		
4 Revision History Changes from Revision C (April 2019) to Re	evision D	(August 2020)	Page
<ul><li>「特長」一覧の値を訂正。</li></ul>			1
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	「行文」 見り進さ訂正。	• • • •
•	文書全体にわたって表、図、相互参照の採番方法を更新	1
•	「 <i>概要</i> 」と「 <i>製品情報</i> 」表を更新	1
•	Deleted incorrect history tags from revision C: Changed 1.65-V to 3.6-V VCC to 1.65-V to 5-V VCC operation	
	and Changed MAX operating temperature to 125°C in Recommended Operating Conditions table	2
•	Changed ESD ratings table to automotive format	4
•	Corrected I <sub>OH</sub> and I <sub>OL</sub> MAX values in <i>Recommended Operating Conditions</i> table	5
•	Corrected Electrical Characteristics table	
•	Removed Switching Characteristics, CL = 15 pF and Switching Characteristics, -40°C to 85°C tables	7
•	Corrected MAX Switching Characteristics values	
•	Removed unneeded columns in Operating Characteristics table	7
•	Removed first image and unused rows in table in Parameter Measurement Information section	8
•	Updated Feature Description section	
•	Fixed cross references in Detailed Design Procedure section	11
	1 IACC Group Teleprotect III Detailed Design 1 recodule Section	
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C	changes from Revision B (April 2008) to Revision C (April 2019)	age
<u>c</u>	Shanges from Revision B (April 2008) to Revision C (April 2019)  ドキュメントを新しい TI データシートのフォーマットに更新、「注文情報」表を削除、「 アプリケーション」一覧と「 製品	age
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# **5 Pin Configuration and Functions**

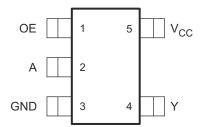


図 5-1. DBV Package 5-Pin SOT-23 Top View



N.C. is no connection

See all mechanical drawings at the end of this data sheet for package dimensions.

図 5-2. DRY Package 6-Pin SON Transparent Top View

#### **Pin Functions**

	PIN			
NAME	DBV (SOT-23)	DRY (SON)	TYPE	DESCRIPTION
A	2	2	I	A Input
GND	3	3	_	Ground Pin
NC	_	5	_	No connection
OE	1	1	I	OE Enable/Input
V <sub>CC</sub>	5	6	_	Power Pin
Y	4	4	0	Y Output



# **6 Specifications**

# **6.1 Absolute Maximum Ratings**

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage range		-0.5	6.5	V
VI	Input voltage range <sup>(2)</sup>		-0.5	6.5	V
Vo	Voltage range applied to any output in the high-impedance or power-off state <sup>(2)</sup>			6.5	V
Vo	Voltage range applied to any output in the high or low state <sup>(2) (3)</sup>		-0.5	V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	Input clamp current	V <sub>I</sub> < 0		-50	mA
I <sub>OK</sub>	Output clamp current	V <sub>O</sub> < 0		-50	mA
Io	Continuous output current			±50	mA
	Continuous current through V <sub>CC</sub> or GND			±100	mA
T <sub>stg</sub>	Storage temperature range		-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## 6.2 ESD Ratings

PARAMETER		DEFINITION	VALUE	UNIT
V	Electrostatic	Human body model (HBM), per AEC Q100-002 <sup>(1)</sup>	±2000	V
V <sub>(ESD)</sub>	discharge	Charged device model (CDM), per AEC Q100-011	±1000	V

(1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

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<sup>(2)</sup> The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

<sup>(3)</sup> The value of V<sub>CC</sub> is provided in the *Recommended Operating Conditions* table.

# **6.3 Recommended Operating Conditions**

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT	
V	Cumply valtage	Operating	1.65	5.5	V	
V <sub>CC</sub>	Supply voltage	Data retention only	1.5	1.5		
		V <sub>CC</sub> = 1.65 V to 1.95 V	0.65 × V <sub>CC</sub>			
V	Lligh level input veltage	V <sub>CC</sub> = 2.3 V to 2.7 V	1.7		V	
V <sub>IH</sub>	High-level input voltage	V <sub>CC</sub> = 3 V to 3.6 V	2		V	
		V <sub>CC</sub> = 4.5 V to 5.5 V	0.7 × V <sub>CC</sub>			
		V <sub>CC</sub> = 1.65 V to 1.95 V		0.35 × V <sub>CC</sub>		
.,	Lauriania in muturalta na	V <sub>CC</sub> = 2.3 V to 2.7 V		0.7	V	
$V_{IL}$	Low-level input voltage	V <sub>CC</sub> = 3 V to 3.6 V		0.8	V	
		V <sub>CC</sub> = 4.5 V to 5.5 V		0.3 × V <sub>CC</sub>		
VI	Input voltage	,	0	5.5	V	
Vo	Output voltage		0	V <sub>CC</sub>	V	
		V <sub>CC</sub> = 1.65 V		-4		
	High-level output current	V <sub>CC</sub> = 2.3 V		-8		
I <sub>OH</sub>		V - 2 V		-16	mA	
		V <sub>CC</sub> = 3 V		-24		
		V <sub>CC</sub> = 4.5 V		-24		
		V <sub>CC</sub> = 1.65 V		4		
		V <sub>CC</sub> = 2.3 V		8		
$I_{OL}$	Low-level output current	V = 2.V		16	mA	
		V <sub>CC</sub> = 3 V		24		
		V <sub>CC</sub> = 4.5 V		24		
		V <sub>CC</sub> = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V		20		
Δt/Δν	Input transition rise or fall rate	V <sub>CC</sub> = 3.3 V ± 0.3 V		10	ns/V	
		V <sub>CC</sub> = 5 V ± 0.5 V		5		
T <sub>A</sub>	Operating free-air temperature	,	-40	125	°C	

<sup>(1)</sup> All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

## **6.4 Thermal Information**

		SN74LV0	SN74LVC1G126-Q1		
	THERMAL METRIC(1)	DBV	DRY	UNIT	
		5 PINS	6 PINS		
$R_{\theta JA}$	Junction-to-ambient thermal resistance	240.9	279.0	°C/W	
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	165.8	182.7	°C/W	
$R_{\theta JB}$	Junction-to-board thermal resistance	143.2	154.5	°C/W	
ΨЈТ	Junction-to-top characterization parameter	84.4	31.3	°C/W	
ΨЈВ	Junction-to-board characterization parameter	142.5	153.8	°C/W	
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	-	_	°C/W	

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.



## **6.5 Electrical Characteristics**

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V <sub>cc</sub>	MIN	TYP <sup>(1)</sup>	MAX	UNIT	
	I <sub>OH</sub> = -100 μA	1.65 V to 5.5 V	V <sub>CC</sub> - 0.1				
	I <sub>OH</sub> = -4 mA	1.65 V	1.2				
V <sub>OH</sub>	I <sub>OH</sub> = -8 mA	2.3 V	1.9			V	
VOH	I <sub>OH</sub> = -16 mA	3 V	2.4			V	
	24 4	3 V	2.3				
	I <sub>OH</sub> = -24 mA	4.5 V	3.8				
	I <sub>OL</sub> = 100 μA	1.65 V to 5.5 V			0.1		
	I <sub>OL</sub> = 4 mA	1.65 V			0.45	V	
V <sub>OL</sub>	I <sub>OL</sub> = 8 mA	2.3 V			0.3		
	I <sub>OL</sub> = 16 mA	3 V			0.4	V	
	L = 24 mA	3 V			0.55	-	
	I <sub>OL</sub> = 24 mA	4.5 V			0.55		
I <sub>I</sub> A or OE inputs	V <sub>I</sub> = 5.5 V or GND	0 to 5.5 V			±5	μA	
l <sub>off</sub>	$V_I$ or $V_O = 5.5 V$	0			±10	μA	
l <sub>oz</sub>	V <sub>O</sub> = 0 to 5.5 V	3.6 V			10	μΑ	
I <sub>cc</sub>	$V_I = 5.5 \text{ V or GND}$ $I_O = 0$	1.65 V to 5.5 V			10	μA	
ΔI <sub>CC</sub>	One input at $V_{CC} - 0.6 \text{ V}$ , Other inputs at $V_{CC}$ or GND	3 V to 5.5 V			500	μΑ	
Ci	V <sub>I</sub> = V <sub>CC</sub> or GND	3.3 V		4		pF	

<sup>(1)</sup> All typical values are at  $V_{CC}$  = 3.3 V,  $T_A$  = 25°C.

# 6.6 Switching Characteristics

over recommended operating free-air temperature range, C<sub>L</sub> = 50 pF (unless otherwise noted) (see  $\boxtimes$  7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = 3 ± 0.3		V <sub>CC</sub> = 9 ± 0.5		UNIT
	(INFOT)	(001701)	MIN	MAX	MIN	MAX	
t <sub>pd</sub>	A	Y	1	5.8	1	4.5	ns
t <sub>en</sub>	OE	Y	1.2	5.8	1	5	ns
t <sub>dis</sub>	OE	Y	1	6	1	4.2	ns

# **6.7 Operating Characteristics**

 $T_A = 25^{\circ}C$ 

PARAMETER		TEST CONDITIONS	V <sub>CC</sub> = 3.3 V TYP	V <sub>CC</sub> = 5 V TYP	UNIT	
C .	Power dissipation capacitance	Outputs enabled	f = 10 MHz	19	21	pF
C <sub>pd</sub>	rower dissipation capacitance	Outputs disabled	tputs disabled f = 10 MHz		4	рΓ

# **6.8 Typical Characteristics**

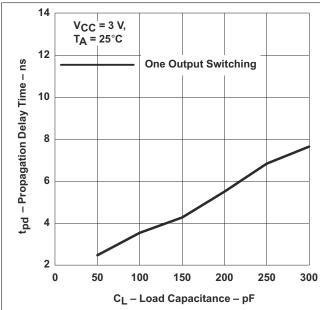


図 6-1. Propagation Delay (Low to High Transition) vs Load Capacitance

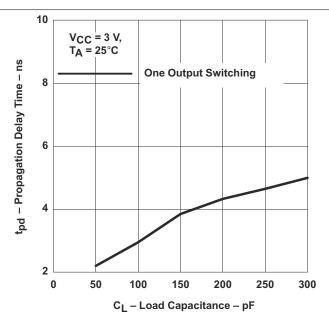
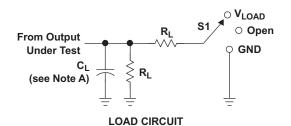


図 6-2. Propagation Delay (High to Low Transition) vs Load Capacitance

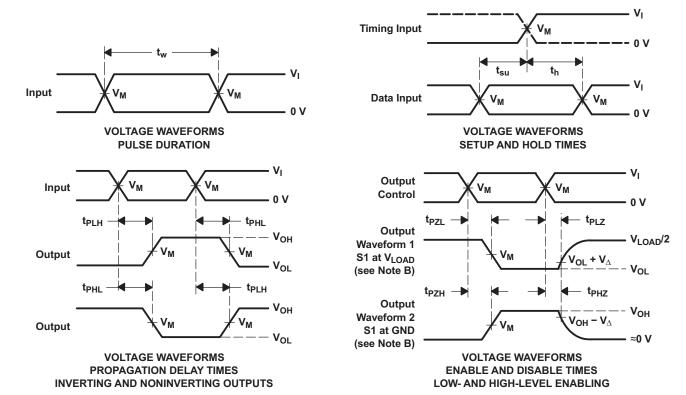


## 7 Parameter Measurement Information



TEST	S1
t <sub>PLH</sub> /t <sub>PHL</sub>	Open
t <sub>PLZ</sub> /t <sub>PZL</sub>	V <sub>LOAD</sub>
t <sub>PHZ</sub> /t <sub>PZH</sub>	GND

.,	INPUTS		.,	.,		_	.,	
V <sub>CC</sub>	VI	t <sub>r</sub> /t <sub>f</sub>	V <sub>M</sub>	V <sub>LOAD</sub>	CL	$R_L$	$oldsymbol{V}_{\!\Delta}$	
3.3 V ± 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	50 pF	<b>500</b> Ω	0.3 V	
5 V ± 0.5 V	$v_{cc}$	≤2.5 ns	V <sub>CC</sub> /2	2 × V <sub>CC</sub>	50 pF	<b>500</b> Ω	0.3 V	



NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR $\leq$  10 MHz, Z<sub>O</sub> = 50  $\Omega$ .
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t<sub>PLZ</sub> and t<sub>PHZ</sub> are the same as t<sub>dis</sub>.
- F. t<sub>PZL</sub> and t<sub>PZH</sub> are the same as t<sub>en</sub>.
- G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .
- H. All parameters and waveforms are not applicable to all devices.

図 7-1. Load Circuit and Voltage Waveforms

## 8 Detailed Description

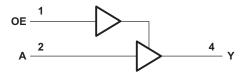
#### 8.1 Overview

The SN74LVC1G126-Q1 device contains a dual buffer gate with output enable control and performs the Boolean function Y = A.

This device is fully specified for partial-power-down applications using I<sub>off</sub>. The I<sub>off</sub> circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

To ensure the high-impedance state during power up or power down, OE should be tied to GND through a pull-down resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

#### 8.2 Functional Block Diagram



#### 8.3 Feature Description

#### 8.3.1 Balanced CMOS 3-State Outputs

This device includes balanced CMOS 3-State outputs. The three states that these outputs can be in are driving high, driving low, and high impedance. The term "balanced" indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

When placed into the high-impedance mode, the output will neither source nor sink current, with the exception of minor leakage current as defined in the *Electrical Characteristics* table. In the high-impedance state, the output voltage is not controlled by the device and is dependent on external factors. If no other drivers are connected to the node, then this is known as a floating node and the voltage is unknown. A pull-up or pull-down resistor can be connected to the output to provide a known voltage at the output while it is in the high-impedance state. The value of the resistor will depend on multiple factors, including parasitic capacitance and power consumption limitations. Typically, a  $10 \text{ k}\Omega$  resistor can be used to meet these requirements.

Unused 3-state CMOS outputs should be left disconnected.

#### 8.3.2 Partial Power Down (I<sub>off</sub>)

This device includes circuitry to disable all outputs when the supply pin is held at 0 V. When disabled, the outputs will neither source nor sink current, regardless of the input voltages applied. The amount of leakage current at each output is defined by the I<sub>off</sub> specification in the *Electrical Characteristics* table.

#### 8.3.3 Standard CMOS Inputs

This device includes standard CMOS inputs. Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law  $(R = V \div I)$ .

Standard CMOS inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in Implications of Slow or Floating CMOS Inputs.

Do not leave standard CMOS inputs floating at any time during operation. Unused inputs must be terminated at  $V_{CC}$  or GND. If a system will not be actively driving an input at all times, a pull-up or pull-down resistor can be



added to provide a valid input voltage during these times. The resistor value will depend on multiple factors, however a  $10-k\Omega$  resistor is recommended and will typically meet all requirements.

#### 8.3.4 Clamp Diode Structure

The inputs and outputs to this device have negative clamping diodes only as depicted in 🗵 8-1.

#### **CAUTION**

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

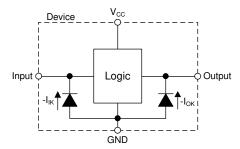


図 8-1. Electrical Placement of Clamping Diodes for Each Input and Output

#### **8.4 Device Functional Modes**

表 8-1. Function Table

INP	JTS	ОИТРИТ
OE	Α	Y
Н	Н	Н
Н	L	L
L	Χ	Z

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# 9 Application and Implementation

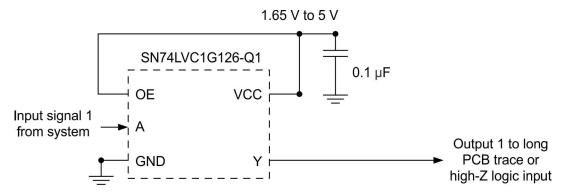
#### Note

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#### 9.1 Application Information

The SN74LVC1G126-Q1 device is a high-drive CMOS device that can be used as an output enabled buffer with a high output drive, such as an LED application. It can produce 24 mA of drive current at 3.3 V, making it ideal for driving multiple outputs and good for high speed applications up to 100 MHz. The inputs are 5.5-V tolerant allowing it to translate down to  $V_{CC}$ .

## 9.2 Typical Application



☑ 9-1. Application Schematic

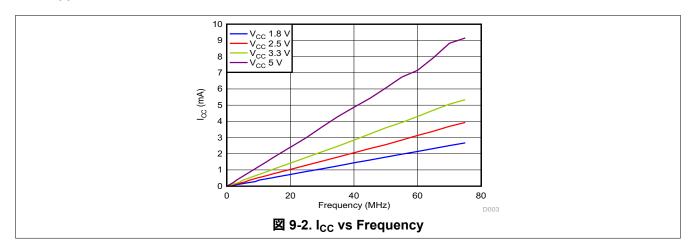
#### 9.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Care should be taken to avoid bus contention because it can drive currents that would exceed maximum limits. Outputs can be combined to produce higher drive but the high drive will also create faster edges into light loads, so routing and load conditions should be considered to prevent ringing.

#### 9.2.2 Detailed Design Procedure

- 1. Recommended Input Conditions:
  - For rise time and fall time specifications, see Δt/ΔV in the Recommended Operating Conditions table.
  - For specified high and low levels, see V<sub>IH</sub> and V<sub>IL</sub> in the Recommended Operating Conditions table.
  - Inputs are overvoltage tolerant allowing them to go as high as 5.5 V at any valid V<sub>CC</sub>.
- 2. Recommend Output Conditions:
  - · Load currents should not exceed 50 mA per output and 100 mA total for the part.

#### 9.2.3 Application Curves



## 10 Power Supply Recommendations

The power supply can be any voltage between the MIN and MAX supply voltage rating located in the *Recommended Operating Conditions* table.

Each  $V_{CC}$  terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- $\mu$ F capacitor is recommended. If there are multiple  $V_{CC}$  terminals, then 0.01- $\mu$ F or 0.022- $\mu$ F capacitors are recommended for each power terminal. It is ok to parallel multiple bypass capacitors to reject different frequencies of noise. Multiple bypass capacitors may be paralleled to reject different frequencies of noise. The bypass capacitor should be installed as close to the power terminal as possible for the best results.

### 11 Layout

### 11.1 Layout Guidelines

When using multiple bit logic devices, inputs should not float. In many cases, functions or parts of functions of digital logic devices are unused. Some examples are when only two inputs of a triple-input AND gate are used, or when only 3 of the 4-buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states.

Specified in Recommended Operating Conditions are rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or  $V_{CC}$ , whichever makes more sense or is more convenient. It is acceptable to float outputs unless the part is a transceiver. If the transceiver has an output enable pin, it will disable the outputs section of the part when asserted. This will not disable the input section of the I/Os so they also cannot float when disabled.

### 11.2 Layout Example

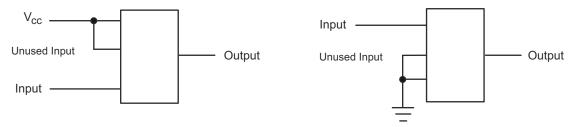


図 11-1. Layout Diagram

# 12 Device and Documentation Support

## 12.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### 12.2 Support Resources

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

#### 12.3 Trademarks

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#### 12.4 静電気放電に関する注意事項



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ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

## 12.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

## 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com 23-May-2025

#### PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	RoHS	Lead finish/	MSL rating/	Op temp (°C)	Part marking
	(1)	(2)			(3)	Ball material	Peak reflow		(6)
						(4)	(5)		
1P1G126QDBVRQ1	Active	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(34Q5, C26O)
1P1G126QDBVRQ1.A	Active	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(34Q5, C26O)
1P1G126QDBVRQ1.B	Active	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(34Q5, C26O)
1P1G126QDRYRQ1	Active	Production	SON (DRY)   6	5000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HN
1P1G126QDRYRQ1.B	Active	Production	SON (DRY)   6	5000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HN

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

<sup>(2)</sup> Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

# PACKAGE OPTION ADDENDUM

www.ti.com 23-May-2025

#### OTHER QUALIFIED VERSIONS OF SN74LVC1G126-Q1:

● Catalog : SN74LVC1G126

● Enhanced Product : SN74LVC1G126-EP

NOTE: Qualified Version Definitions:

• Catalog - TI's standard catalog product

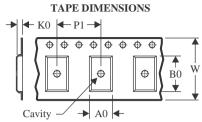
• Enhanced Product - Supports Defense, Aerospace and Medical Applications

# **PACKAGE MATERIALS INFORMATION**

www.ti.com 24-Jan-2025

## TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

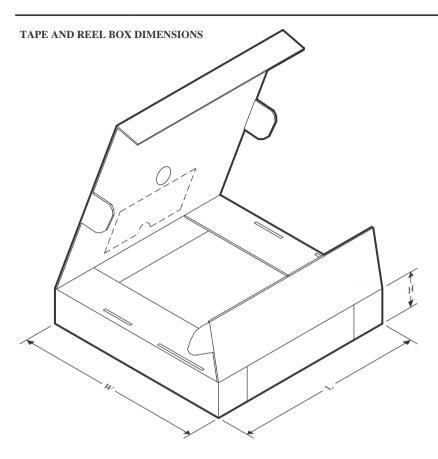
#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device		Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
1P1G126QDBVRQ1	SOT-23	DBV	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
1P1G126QDRYRQ1	SON	DRY	6	5000	180.0	9.5	1.2	1.65	0.7	4.0	8.0	Q1

www.ti.com 24-Jan-2025



#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
1P1G126QDBVRQ1	SOT-23	DBV	5	3000	190.0	190.0	30.0
1P1G126QDRYRQ1	SON	DRY	6	5000	189.0	185.0	36.0



SMALL OUTLINE TRANSISTOR



#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  2. This drawing is subject to change without notice.
  3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





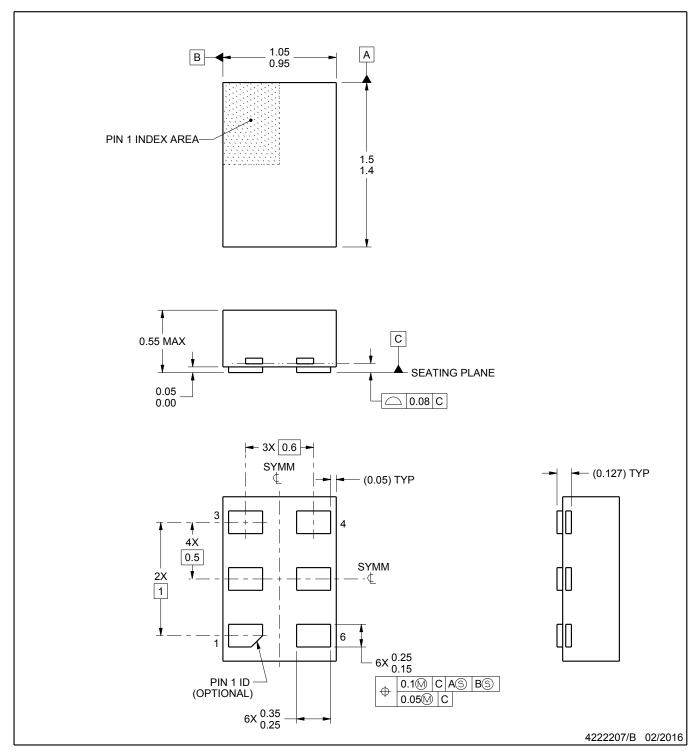
Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.







PLASTIC SMALL OUTLINE - NO LEAD



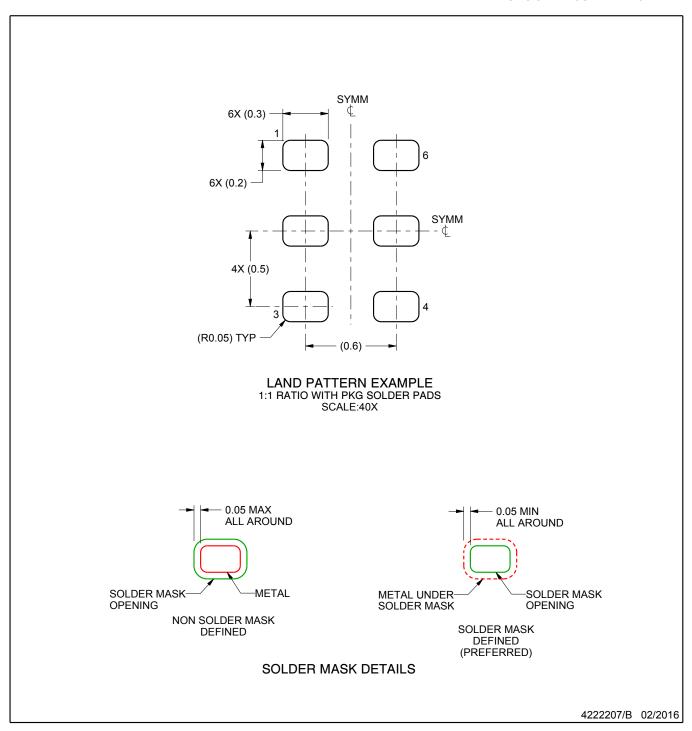
#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.



PLASTIC SMALL OUTLINE - NO LEAD

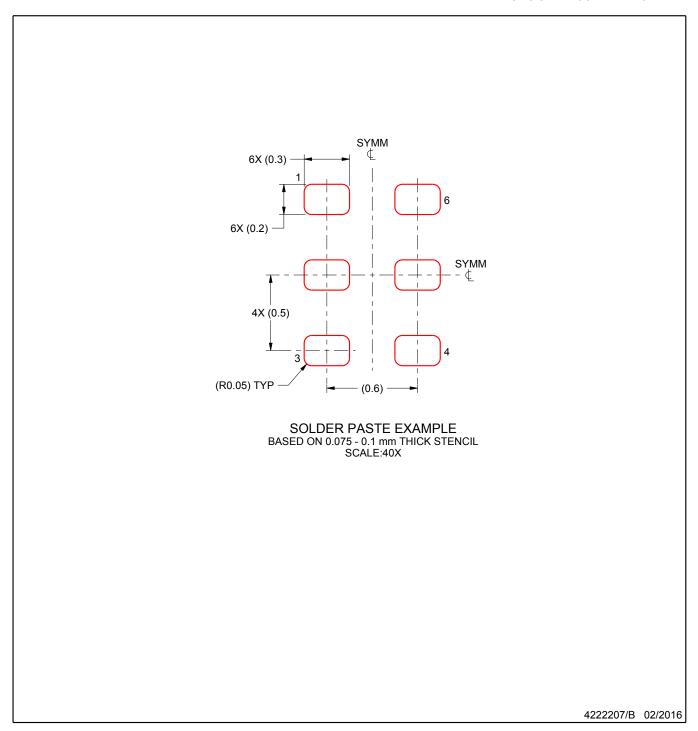


NOTES: (continued)

3. For more information, see QFN/SON PCB application report in literature No. SLUA271 (www.ti.com/lit/slua271).



PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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